In the Claims

1. (currently amended) A process for preparing a dry film resist, ~~by~~ which process comprises forming a photocurable resin composition onto a support film with a thickness of 1 to 50 µm and optionally laminate a protective film onto the photocurable composition layer to obtain a dry film resist; whereby the photocurable resin is formed from a homogeneous mixture comprising

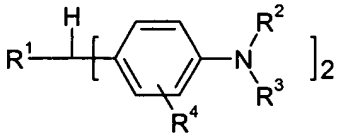
(a) from 20-90wt% of an alkaline soluble binder oligomer or polymer;

(b) from 5 to 60wt% of one or more photopolymerizable monomers which are compatible with the oligomers and polymers of component (a);

(c) from 0.01 to 20% by weight of one or more photoinitiators;

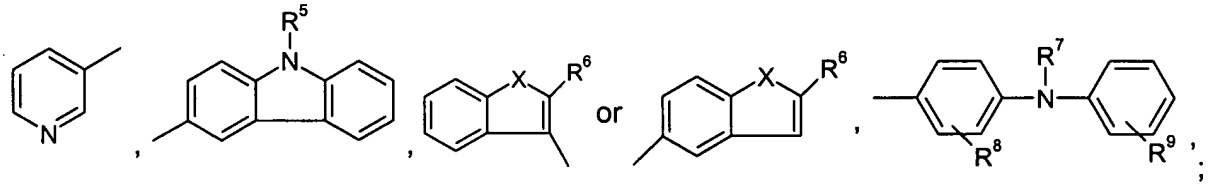
(d) from 0 to 20% by weight of additives and/or assistants; and

(e) from 0.1 to 10 % by weight of a leuco triphenylmethane dye of the formula I



wherein

R^1 is a residue selected from



R^2 is C_1-C_{12} alkyl or phenyl which may be mono-, di- or tri-substituted by C_1-C_6 alkyl, trifluoromethyl, C_1-$_6$ alkoxy, C_1-$_6$ alkylthio, halogen and nitro;

R^3 is hydrogen or C_1-C_{12} alkyl;

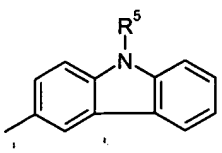
R^4 to R^9 independently of one another are hydrogen or C_1-C_{12} alkyl; and

X is O, S, NH or N-C_1-C_{12}-alkyl;

(a) to (e) being 100% by weight.

2. (currently amended) A process according to claim **1**, wherein in formula I

R^1 is a residue ~~selected from~~



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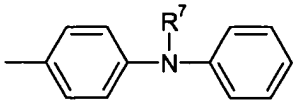


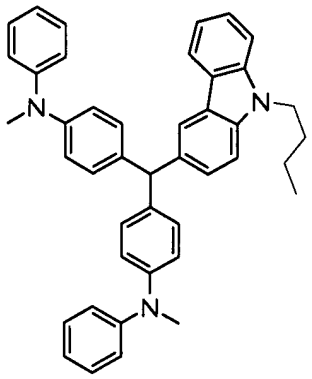
R^2 is unsubstituted phenyl,

R^3 is C_1-C_4alkyl

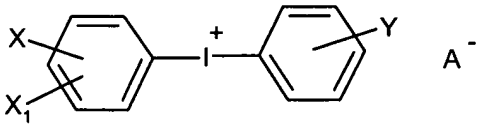
R^4 is hydrogen; and

R^5 and R^7 are C_1-C_4alkyl.

3. (currently amended) A process according to claim **1**, wherein the leuco triphenylmethan dye is 4,4'-[(9-Butyl-9H-carbazol-3-yl)methylene]bis[N-methyl-N-phenylaniline of the formula



4. (currently amended) A process according to claim 1~~any one of claims 1-3~~, wherein component d) includes a diaryliodonium of formula



wherein

X is branched C_3-C_{20}alkyl or C_3-C_8cycloalkyl;

X_1 is hydrogen, linear C_1-C_{20}alkyl, branched C_3-C_{20}alkyl or C_3-C_8cycloalkyl; with the proviso that the sum of the carbon atoms in X and X_1 is at least 4;

Y is linear C_1-C_{10}alkyl, branched C_3-C_{10}alkyl or C_3-C_8cycloalkyl;

A^- is a non-nucleophilic anion, selected from the group consisting of $(BF_4)^-$, $(SbF_6)^-$, $(PF_6)^-$, $(B(C_6F_5))_4^-$, C_1-C_{20}alkylsulfonate, C_2-C_{20}haloalkylsulfonate, unsubstituted C_6-C_{10}arylsulfonate, camphor-sulfonate, C_1-C_{20}-perfluoroalkylsulfonylmethide, C_1-C_{20}-perfluoroalkylsulfonylimide, and C_6-C_{10}arylsulfonate substituted by halogen, NO_2, C_1-C_{12}alkyl, C_1-C_{12}halo-alkyl, C_1-C_{12}alkoxy or by $COOR_1$; and

R_1 is C_1-C_{20}alkyl, phenyl, benzyl; or phenyl mono- or poly-substituted by C_1-C_{12}alkyl, C_1-C_{12}alkoxy or by halogen.

5. (currently amended) A dry film resist obtainedable by a process according to claimany one of claims **1[[-4]]**.

6. (currently amended) A process for preparing a dry film resist element comprising the steps of

(A) forming a photocurable resin composition layer made of ingredients (a)-(e) according to claim 1as defined above onto a support film with a thickness of 1 to 50 µm, and laminate a protective film onto the photocurable composition layer to obtain a dry film resist;

(B) removing the protective film before use, and thermally laminate the photocurable composition layer onto the surface of a desired substrate for the application of the dry film resist at 100-150°C;

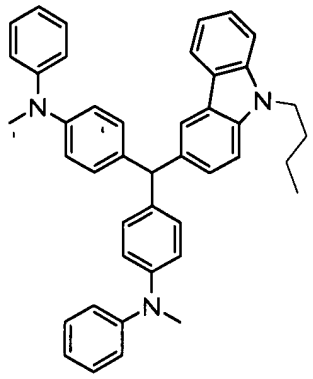
(C) exposure to radiation through a mask or by direct laser irradiation; and

(D) removing the support film and wash away the unexposed (uncured) area by development.

7. (currently amended) A dry film resist element obtainedable by a process according to claim **6**.

8. (canceled)

9. (currently amended) The use of A process according to claim **6** wherein component (e) is 4,4'-[(9-butyl-9H-carbazol-3-yl)methylene]bis[N-methyl-N-phenylaniline of the formula



~~to form a photocurable resin composition as defined in claim 1 to avoid unfavourable colour generation during the heat lamination of the photocurable composition layer onto the surface of a desired substrate for the application of the dry film resist at 100-150°C~~.

10. (currently amended) A process~~The use of the dry film resist element~~ according to claim ~~6~~7 for forming copper circuit pattern of printed circuit board, ~~and~~ LSI packaging ~~like~~ etching resist or~~and~~ plating resist, for solder resist or~~and~~ for forming cell or electrode pattern in ~~various~~ flat display panel applications.